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ABSTRACT

ABRASIVE, METHOD OF POLISHING TARGET MEMBER AND PROCESS FOR PRODUCING SEMICONDUCTOR DEVICE

To polish polishing target surfaces of SiO_2
insulating films or the like at a high rate without
scratching the surface, the present invention provides an
5 abrasive comprising a slurry comprising a medium and
dispersed therein at least one of i) cerium oxide particles
constituted of at least two crystallites and having crystal
grain boundaries or having a bulk density of not higher than
6.5 g/cm³ and ii) abrasive grains having pores. Also
10 provided are a method of polishing a target member and a
process for producing a semiconductor device which make use
of this abrasive.